- V_{CE} =1200V
- = Ǝ

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V_{CES}	Collector-emitter voltage	1200	V
V_{GES}	Gate-emitter voltage	±20	V
I_C	Continuous collector current (T_C=25)	150	A
	Continuous collector current (T_C=100)	75	A
I_{CM}	Pulsed collector current, t_p limited by T_{vjmax}	300	A
I_F	Diode continuous forward current (T_C=100)	75	A
I_{FM}	Diode maximum current, t_p limited by T_{vjmax}	150	A
t_{sc}	Short circuit withstand time	10	μs
P_{tot}	Power dissipation (T_C=25)	882	W
	Power dissipation (T_C=100)	441	W
T_{vj}	Operating junction temperature range	-40 to +175	
T_{stg}	Storage temperature range	-55 to +150	

$R_{th(j-c)}$	Thermal resistance, junction to case for IGBT	-	0.17	K/ W
$R_{th(j-c)}$	Thermal resistance, junction to case for Diode	-	0.35	K/ W
$R_{th(j-a)}$	Thermal resistance, junction to ambient	-	40	K/ W

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BV_{CES}	Collector-emitter breakdown voltage	V_{GE}=0V, I_C=250μA	1200	-	-	V
I_{CES}	Collector-emitter leakage current	V_{CE}=1200V, V_{GE}=0V	-	-	100	μA
I_{GES}	Gate leakage current, forward	V_{GE}=20V, V_{CE}=0V	-	-	100	nA
	Gate leakage current, reverse	V_{GE}=-20V, V_{CE}=0V	-	-	-100	nA
$V_{GE(th)}$	Gate-emitter threshold voltage	V_{GE}=V_{CE}, I_C=1mA	5.0	5.5	6.0	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE}=15 V, I_C=75A	-	1.7	-	V
		V_{GE}=15V, I_C=75A, T_{vj}=175	-	2.2	-	V

C_{ies}	Input capacitance		-	6800	-	pF
C_{oes}	Output capacitance	V_{CE}=30V V_{GE}=0V f=1MHz	-	350	-	

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(T_{vj}=25 unless otherwise specified)

V_F	Diode forward voltage	I_F=75A	-	1.8	-	V
		I_F=75A T_{vj}=175	-	1.5	-	V
t_{rr}	Diode reverse recovery time	V_R=600V I_F=75A di_F/dt=-200A/μs	-	364	-	ns
I_{rrm}	Diode peak reverse recovery current		-	11	-	A
Q_{rr}	Diode reverse recovery charge		-	2300	-	nC
t_{rr}	Diode reverse recovery time	V_R=600V I_F=75A di_F/dt=-200A/μs T_{vj}=175	-	576	-	ns
I_{rrm}	Diode peak reverse recovery current		-	23	-	A
Q_{rr}	Diode reverse recovery charge		-	8300	-	nC

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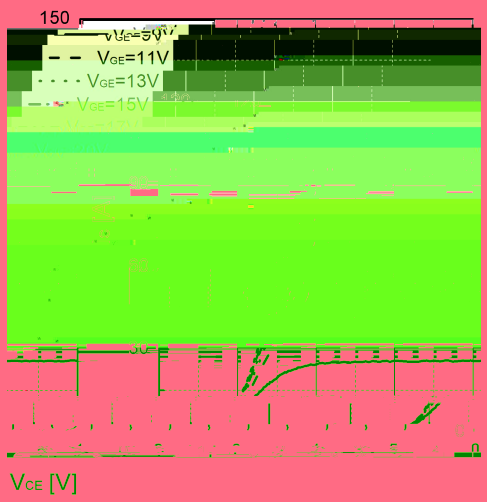

Fig 1. Typical output characteristic (T_{vj}=25)

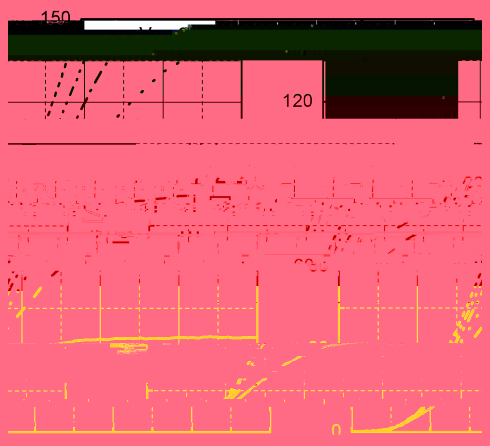

Fig 2. Typical output characteristic(T_{vj}=175)

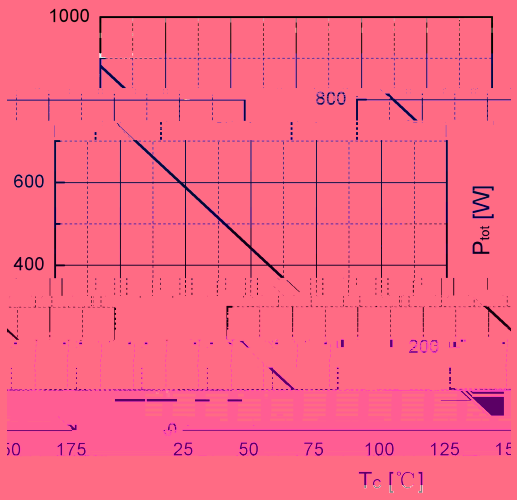

Fig 3. Power dissipation as a function of T_C

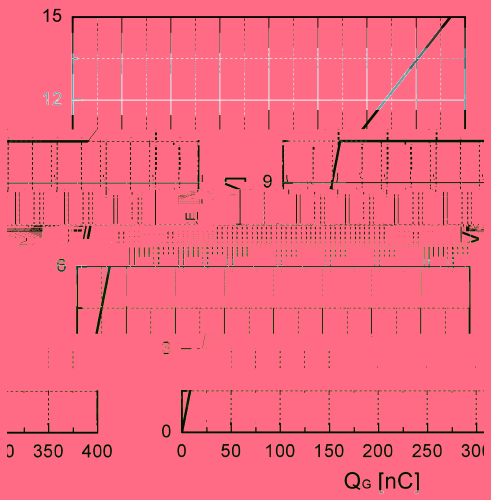

Fig 4. Typical Gate charge

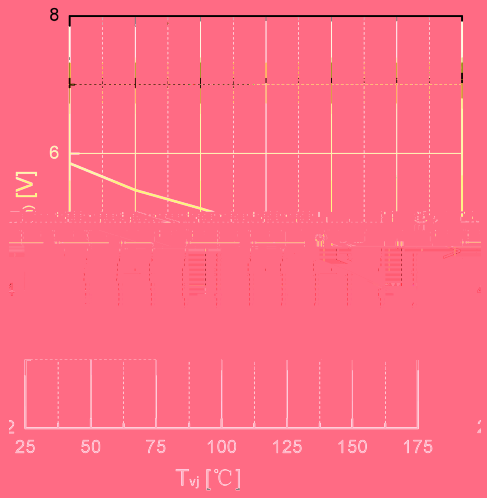

Fig 5. Typical $V_{GE(th)}$ as a function of T_{vj} (I_C=1mA)

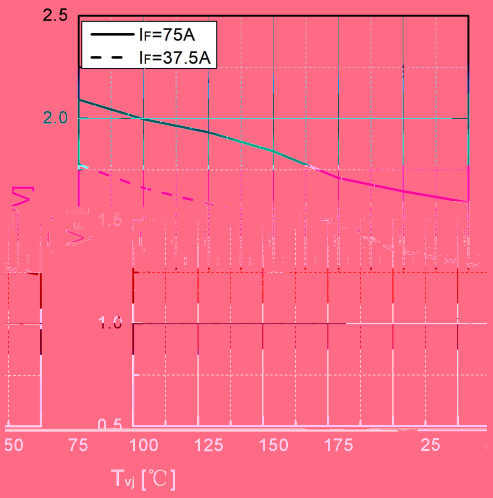

Fig 6. Typical V_F as a function of T_{vj}

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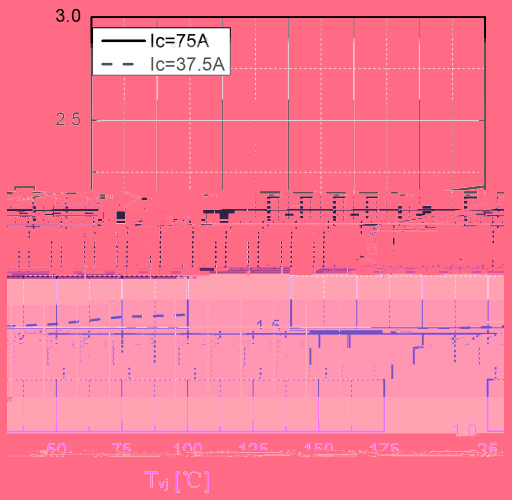

Fig 7. Typical V_{CEsat} as a function of T_{vj}

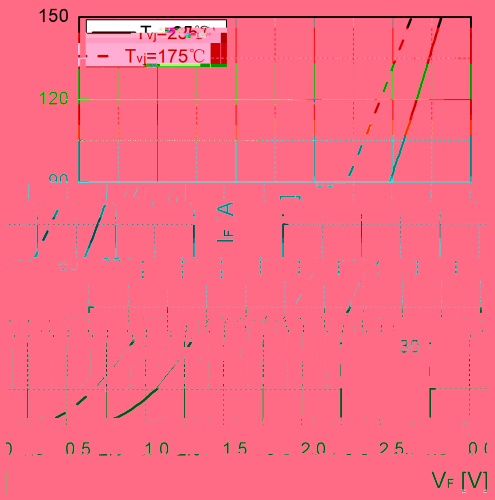

Fig 8. Typical I_F as a function of V_F

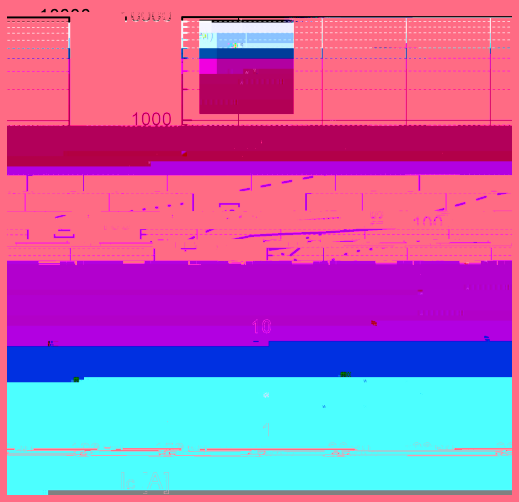

Fig 9. Typical switching time as a function of I_C

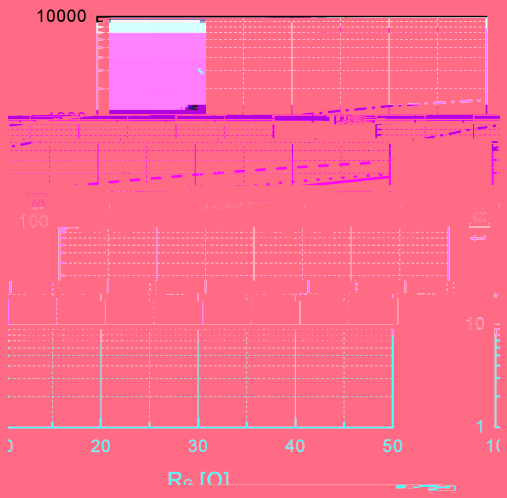

Fig 10. Typical switching times as a function of R_G

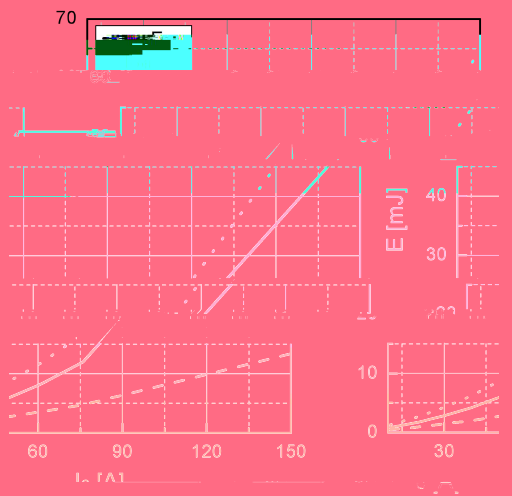

Fig 11. Typical switching energy losses as a function of I_C

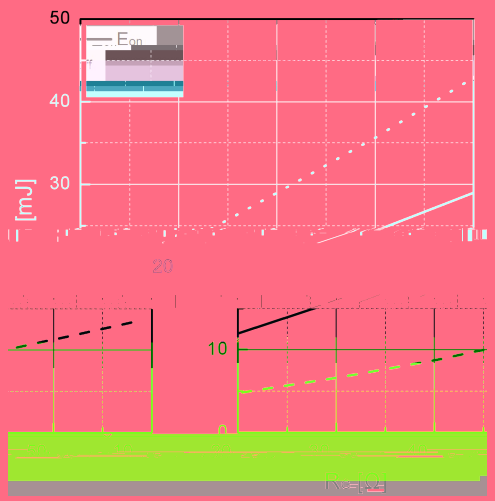

Fig 12. Typical switching energy losses as a function of R_G

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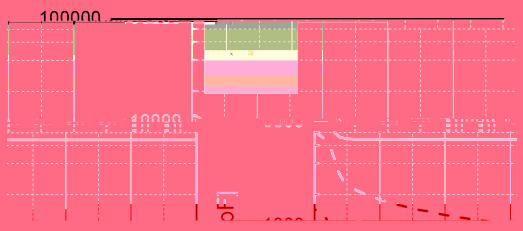

Fig 13. Typical capacitance as a function of V_{CE}
(f=1Mhz, V_{GE}=0V)

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Date	Revision	Changes
2024-08-26	Rev. 1.2	Update
2025-02-17	Rev. 1.3	Modify the package size
2025-03-03	Rev. 2.0	Replace sketch

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